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1
2 **METHOD AND APPARATUS FOR ABLATIVE**
3 **BONDING USING A PULSED ELECTRON BEAM**
4

5 **BACKGROUND OF THE INVENTION**

6 The present invention generally relates to the field of lami-
7 nate coatings and more particularly, is directed to a method and
8 apparatus for bonding or cladding a layer of material onto a sub-
9 strate with minimal bulk heating of the substrate.

10 There are a variety of techniques known in the prior art for
11 bonding or cladding a layer of dissimilar material onto a sub-
12 strate. Known techniques which produce enhanced bonding between
13 the coating and the substrate include:

- 14 1. Static processes;
15 2. Thermal spray processes;
16 3. Conventional and explosive welding; and
17 4. Laser, microwave and electron beam joining.

18 Static process techniques include such conventional approaches
19 as adhesive joining, cladding and brazing. Simple adhesives are,
20 however, impractical in many cases while conventional cladding
21 usually involves the simultaneous application of intense heat and
22 pressure. This is a slow process which results in considerable
23 bulk heating of the substrate. In brazing, a heat-absorbing braz-
24 ing material is placed between the coating and the substrate.
25 Conventional brazing again causes substantial heating of the sub-
26 strate and often produces a relatively weak bond.

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1 Thermal spray processes are widely used to apply coatings,
2 particularly in cases where the coating does not bond well to the
3 substrate. The typical thickness of such coatings is 100 microns.
4 The process typically involves heating the coating material in
5 powder form to molten temperatures and blasting it onto the sub-
6 strate at speeds of 500 m/s. Thus, both heat and pressure (in the
7 form of the droplet kinetic energy) is involved in the bonding
8 process. Although this technology has been available commercially
9 for decades, and the coating quality can be excellent, the capital
10 cost of devices such as plasma sprayers and detonation guns is
11 substantial. The processing cost of such coatings commonly exceeds
12 a dollar per square inch. Also, the process is not appropriate if
13 the applied layer is already in the form of a plate or film (i.e.,
14 for cladding). The terms "coating" and "cladding", although
15 sometimes used interchangeably, more properly refer to different
16 application processes. Cladding refers to bonding a plate or film
17 to a workpiece, while coating refers to a bonding process that also
18 changes the form of the material being bonded (e.g., applying
19 liquids or powdered solids to a workpiece). Preferably, an im-
20 proved bonding process will work for both coating and cladding
21 applications.

22 If the coating and substrate are metallurgically compatible or
23 "weldable", then conventional welding techniques may be used. This
24 process is sometimes referred to as fusion hardfacing. Fusion
25 hardfacing cannot be used in cases where the substrate cannot be
26 heated or the materials are not weldable. Difficult to weld mate-

1 . rials such as titanium can often be bonded to other materials by an
2 explosive welding process. A small amount of high explosives is
3 used to accelerate a flyer plate which drives the materials togeth-
4 er. However, explosive welding is often not suitable to high
5 volume processing, and there is little control over the process.

6 Many bonding processes involving advanced heat sources such as
7 lasers, microwave, and electron beams have been proposed, but few
8 are used commercially. Both lasers and continuous (DC) electron
9 beams have been used for fusion hardfacing. Lasers are relatively
10 inefficient and must rely on thermal conduction to heat the coat-
11 ing-substrate interface unless the coating is transparent to the
12 laser. Microwaves are similar to electron beams in that they can
13 produce rapid heating into the depth of the coating layer, provided
14 that the coating is not highly conducting. Although these process-
15 es produce controlled, localized heating, they do not in general
16 produce the additional pressure which is often required for a
17 strong bond between dissimilar materials. In addition, most are
18 not suitable for high volume industrial applications.

19 20 SUMMARY OF THE INVENTION

21 For the above reasons, there is a need in the prior art for an
22 improved method and apparatus for coating or cladding a layer of
23 material onto a substrate with minimal bulk heating of the sub-
24 strate.

25 Accordingly, it is the overall object of the present invention
26 to provide an improved method of coating or cladding a layer of

1 material onto a substrate which overcomes the above noted disadvan-
2 tages of such methods known in the prior art.

3 It is a specific object of the present invention to provide an
4 improved method of bonding a layer of material to a substrate which
5 is more efficient than such methods known in the prior art with
6 respect to the results achieved.

7 It is a still further specific object of the present invention
8 to provide an improved method of bonding a layer of material to a
9 substrate that is potentially lower in cost than plasma sprays.

10 It is a still further specific object of the present invention
11 to provide an improved method of bonding a layer of material to a
12 substrate which can be used with many more types of materials than
13 such methods known in the prior art, including powders, plates,
14 films, liquids, metals, ceramics, and composites.

15 It is a still further specific object of the present invention
16 to provide an improved method of bonding a layer of material to a
17 substrate which can be used in much higher volume applications than
18 many of the methods known in the prior art.

19 It is a still further specific object of the present invention
20 to provide an improved method of bonding a layer of material to a
21 substrate from a layer of material at a standoff distance from the
22 substrate.

23 It is another object of the present invention to provide an
24 improved method of bonding a layer of material to a substrate which
25 provides greater process control, minimal substrate heating, and

1 superior bonding strength in comparison to such methods known in
2 the prior art.

3 These and other objects of the present invention are achieved
4 by a combination of rapid in-depth heating and pressure generated
5 by a pulsed electron beam. The method can be applied to many coat-
6 ing layer materials, including metals, alloys, ceramics, polymers,
7 and composites. The coating can also be in the form of a thin
8 plate, a film, or a powder. The typical electron beam source used
9 in accordance with the method of the invention has a peak energy of
10 50-500 keV, a pulse length of 1 microsecond, and peak currents of
11 0.1-10 kA.

12 The invention uses a pulsed electron beam generator which
13 produces high energy electrons at the beginning of the pulse and a
14 larger number of lower energy electrons at the end of the pulse.
15 A thin sacrificial layer of an easily-vaporized material such as
16 tin is placed on top of the coating. The high energy electrons
17 penetrate through the sacrificial layer and the coating layer,
18 heating them to a molten temperature in a fraction of a microsec-
19 ond. The lower energy electrons are stopped by the sacrificial
20 layer, causing it to ablate or vaporize. The ablation process
21 generates a force or pressure pulse on the coating which drives it
22 into the substrate. The bond type which is formed is primarily
23 mechanical and is referred to as a nonfusion bond since the coating
24 and substrate do not form a solid solution.

25 Alternatively, two separate pulsed electron beam generators
26 may be used instead of a single pulsed electron beam generator:

1 one electron beam generator for generating a pulse of high energy
2 electrons, and one electron beam generator for generating a higher
3 current pulse of lower energy electrons. The advantage of this
4 approach is that it may be simpler and more cost effective to
5 provide two pulsed electron beam generators, each being optimized
6 to its particular function, rather than providing a single electron
7 beam generator that must adequately perform both of these func-
8 tions.

9 The coating process of the invention can be optimized by
10 adjusting the time history of the beam energy and current to local-
11 ize the energy deposition and control the temperature of the sacri-
12 ficial and coating layers. However, the success of the process is
13 not sensitive to the details of the beam tuning.

14 The coating method of the invention was demonstrated by bond-
15 ing a molybdenum layer to a titanium substrate using tin as the
16 ablator. The tin appeared to be completely vaporized by low energy
17 electrons at the end of the beam pulse. No bonding was produced
18 when the tin ablator was removed.

19 Until very recently, pulsed electron beam technology has been
20 generally considered too expensive and unreliable for most indus-
21 trial applications. However, recent advances in developing pulsed
22 electron beam sources with high repetition rates, lower capital
23 cost, high average power, and improved reliability make commercial-
24 ization of this technology now feasible. The techniques can be used
25 in high volume processing involving average beam powers of tens or
26 hundreds of kilowatts.

1 **BRIEF DESCRIPTION OF THE DRAWINGS**

2 The present invention will now be described with reference to
3 the drawings in which:

4 Figure 1 provides an overview of the ablative bonding process
5 in accordance with the present invention;

6 Figure 2 is a block diagram of the components used to imple-
7 ment the ablative bonding method of the present invention;

8 Figure 3 is a graph showing the electron penetration range in
9 various materials as a function of initial electron beam energy;

10 Figure 4 is a block diagram illustrating one embodiment of the
11 ablative bonding method of the present invention, corresponding to
12 an apparatus used in a proof-of-principle experiment;

13 Figure 5 is graph showing experimentally-measured voltage and
14 current vs time from the ablative bonding embodiment illustrated in
15 Figure 4; and

16 Figure 6 is graph plotting a theoretical calculation of
17 specific energy in joules per gram against depth for the embodiment
18 illustrated in Figure 4, and the data from Figure 5.

19
20 **DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT**

21 The method of the present invention is illustrated in Figure
22 1. Figure 1 shows a substrate 1 to which a coating 2 is applied
23 through an ablator layer 3. Layer 3 is a thin sacrificial layer of
24 an easily-vaporized material such as tin which is placed on top of
25 coating 2. High energy electrons 4 penetrate through ablator layer
26 3 and coating layer 2, heating them to a molten temperature in a

1 fraction of a microsecond. The lower energy electrons are stopped
2 by the ablator layer 3, causing it to ablate or vaporize. The
3 ablation process generates a force or pressure pulse on coating 2
4 which drives it into substrate 1. The bond type which is formed is
5 primarily mechanical and is referred to herein as a nonfusion bond
6 since coating layer 2 and substrate 1 do not form a solid solution.

7 The components which form the pulsed electron beam source
8 which performs the method of the present invention are illustrated
9 in Figure 2.

10 These components include a power supply 20 which supplies
11 electrical power to pulsed power module 21 which in turn provides
12 pulse shaping and voltage multiplication. Power module 21 also
13 includes a control device (not shown) which controls the generation
14 of the pulse. An output switch 22 directs the pulse to a diode 23
15 where electrons are generated at the negative cathode and flow
16 towards the positive anode. Alternatively, output switch 22 may be
17 placed ahead of some of the pulsed power components.

18 An optional transition section 24 may be used to provide
19 additional beam focusing. Electromagnets can be used to form
20 transition section 24 so that electron beam 25 can be focused on
21 workpiece 26.

22 The cathode and anode of diode 23 must remain in a high vacuum
23 to avoid electrical breakdown. In the simplest configuration,
24 workpiece 26 is also under vacuum, so the focusing and beam trans-
25 port can be more easily made. If workpiece 26 is in air or some
26 other dense working gas, then transition section 24 must also

1 provide a suitable vacuum/gas transition. In a one-time use of the
2 method of the invention, a vacuum/gas transition could be formed of
3 a thin foil. However, a practical repetitively-pulsed device would
4 require a differential pumping section since the foil would be
5 destroyed by the beam. Differential pumping devices permit the gas
6 pressure to be much higher at the workpiece than in the diode.

7 Although there are a number of physical processes involved in
8 the generation and transport of the electron beam, the ablative
9 bonding process primarily involves the reaction of the workpiece to
10 the beam electrons. Energetic electrons lose energy continuously
11 as they pass through dense material. This energy is deposited into
12 the workpiece in the form of a temperature rise and an increase in
13 internal energy. The depth or range into the material at which
14 electrons lose all their energy is plotted as a function of initial
15 energy E_0 for several materials in Figure 3. A 50 keV electron has
16 a range R of approximately 10 microns in most solid materials. The
17 range typically increases by a factor of 15 when the beam energy is
18 raised to 250 keV.

19 The temperature increase ΔT arising from the energy deposited
20 in the workpiece can be estimated from the specific heat C_v and
21 stopping power dE/dx' of the material and the energy fluence F_b of
22 the beam. The stopping power is typically ~ 1.5 Mev-cm²/g for a 250
23 keV electron beam and ~ 4 MeV-cm²/g at 50 keV. If the current
24 density J_b and voltage V_b are constant during the pulse, then
25 $F_b = J_b V_b \tau_p$, where τ_p is the duration of the pulse. If the tempera-
26 ture T remains below the melting point T_m , the workpiece thickness

1 x is much smaller than R, and thermal conductivity and radiation
2 losses are neglected, then $\Delta T = F_b dE/dx' / C_v$. The specific energy
3 ϵ_{d1} deposited in the material, which is usually expressed in
4 Joules/g, is approximately $\epsilon_{d1} = F_b (dE/dx') / W_0$, where W_0 is the beam
5 energy. The situation is somewhat more complicated if $R < \Delta x$ since
6 dE/dx increases rapidly at the end of the range. In this case, the
7 specific deposition is approximately $\epsilon_{d2} = F_b / R'$, with the reduced
8 range R' usually expressed in g-cm². Once the material is raised
9 to the melting or vaporization temperature, additional energy is
10 required to complete the phase change to the next state. For many
11 materials, the energy required to overcome this heat of vaporiza-
12 tion barrier is substantially larger than the energy required to
13 raise T from room temperature to the vaporization temperature T_v .

14 Ideally, the parameters of electron beam 25 are chosen so that
15 the first part of the pulse penetrates through ablator layer 3 and
16 coating layer 2, heating both to near the melting temperature.
17 This typically requires a specific deposition of several hundred
18 J/g. Due to a process called impedance collapse, the later part of
19 the pulse has a much lower voltage but higher current, so most of
20 those electrons are stopped in the ablator. (In most electron beam
21 devices, impedance collapse is strongly undesirable, and a crowbar
22 switch is added to prevent the burst of low energy electrons at the
23 end of the pulse; however, these electrons are essential to the
24 bonding process in the present invention.) Thus, the specific
25 deposition in the ablator can be substantially higher than in the
26 coating or substrate.

1 Complete vaporization of the ablator layer requires more than
2 10 kJ/g for many materials. However, tin has a low heat of vapor-
3 ization and requires only 2.5 kJ/g for complete vaporization, so it
4 is a useful material for a demonstration experiment.

5 If most of the beam energy is absorbed in the ablator, the
6 heated vapors provide a pressure pulse which drives the coating and
7 substrate together. An estimate of the average pressure is given
8 by $\langle P \rangle = v_r \rho_s \Delta x_{ab} / \tau_{ab}$, where v_r is the "rocket" exhaust velocity of
9 the vaporized material, ρ_s is the solid density of the ablator, Δx_{ab}
10 is the ablator thickness, and τ_{ab} is the duration of the low energy,
11 high current "tail" of the electron pulse which provides most of
12 the heating to the ablator. More detailed theoretical treatments of
13 this process can be made using hydrodynamic computer codes. Such
14 codes have been extensively used to study inertial fusion targets.
15 Pressures of several kbar are required to duplicate the impact
16 associated with typical thermal spray process.

17 A simple proof-of-principle of the present invention was
18 performed using a long pulse electron beam. The arrangement is
19 shown schematically in Figure 4 and includes a cathode stalk 41,
20 carbon cathode tip 42, target 43, anode foil 44, vacuum chamber 45
21 and current monitor 46. Current monitor 46 monitors the level of
22 current in target 43.

23 The electrons were transported in a vacuum, and the workpiece
24 was mounted directly on the anode. The workpiece consisted of
25 three thin strips: a tin ablator, a molybdenum "coating", and a
26 titanium substrate. Each strip was approximately 0.5 mil (12.5

1 microns) thick. The workpiece was mounted on a square 6.25 cm²
2 carbon block.

3 The beam voltage and current traces are shown in Figure 5. The
4 main part of the pulse had a voltage of 240 kV, a current of 300 A,
5 and a duration of 1.5 μ sec. The crowbar switch which normally
6 minimizes impedance collapse was disabled. As the voltage collapsed
7 in the tail of the pulse, the current exceeded 1.5 kA, and the
8 voltage steadily decayed to ten of kilovolts. The fluence is
9 estimated to be 17 J/cm² in the main part of the pulse and 20-25
10 J/cm² in the lower voltage tail. Electrons during the main part of
11 the pulse would have penetrated through to the substrate, deposit-
12 ing only a few hundred J/g in the molybdenum coating. An additional
13 deposition of several hundred J/g probably occurred as the voltage
14 dropped down to ~100 kV. Most of the deposition in the tin ablator
15 probably occurred late in the pulse when the voltage V(t) was
16 between 40 and 100 kV.

17 More detailed estimates of the specific deposition for this
18 case were made using a widely-used Monte Carlo computer simulation
19 model which traces the energy loss and scattering of a large number
20 of electrons in the 6.25 cm² solid target. For simplicity, the
21 electron beam is represented as having two components: a high
22 energy head with an energy of 240 keV, a current of 300 A and
23 duration of 1.5 μ sec, and a lower energy beam tail with an energy
24 of 50 keV, a current of 2000 A and a duration of 1.5 μ sec. Figure
25 6 plots the specific energy or "dose" in joules per gram against
26 the depth onto the target for both beam components, as predicated

1 by the Monte Carlo model. Also shown is the depth corresponding to
2 the tin ablator, the molybdenum cladding layer, and the titanium
3 substrate. The high energy component penetrates well into the
4 substrate, producing a specific deposition of 300-400 J/g. The low
5 energy beam tail penetrates only a few microns into the tin, but
6 has a peak specific deposition of over 7000 J/g. This is well above
7 the 2500 J/g required to vaporize the tin. Since the actual beam
8 energy and current vary continuously during the pulse, the actual
9 deposition profile is some complicated combination of the two
10 curves shown in Figure 6. This computer model result is consistent
11 with the experimental results and with the interpretation of those
12 results herein.

13 Examination of the workpiece revealed that the titanium and
14 molybdenum had bonded together. The sacrificial tin layer appeared
15 to have been completely vaporized. A similar experiment with the
16 tin layer removed showed no evidence of bonding. Because of the
17 much higher vaporization temperature and heat of vaporization of
18 molybdenum compared with tin, much less vaporization would have
19 occurred, and the pressure pulse would have been much weaker. This
20 suggests that the force provided by the ablation process was
21 crucial to forming a strong bond.

22 When compared to the prior art coating processes, e.g., the
23 static process described above, the electron beam ablative bonding
24 method of the present invention offers much more process control,
25 minimal substrate heating, and superior bonding strength. Thermal
26 spray coatings are typically applied at rates of a few cm²/s and

1. require that the coating be in a powder form. Electron beam
2 ablative bonding can have a much higher throughput and can also
3 permit cladding of thin sheets as well as powders onto a substrate.
4 Conventional welding hardfacing techniques are inexpensive but
5 slow, and cannot be used with nonweldable materials. Explosive
6 welding can eliminate the weldability constraints, but the process
7 is cumbersome and difficult to control. Laser, microwave, and DC
8 electron beam joining all have limitations which were discussed
9 above.

10 None of the prior art methods use the pressure pulse employed
11 in e-beam ablative bonding and thus may encounter difficulties in
12 bonding dissimilar materials. The ablative bonding technique of
13 the present invention are inherently more efficient and can more
14 easily be employed in high throughput applications.

15 In general, it is simpler to transport the electron beam in a
16 vacuum as was described above. Direct current electron beam
17 devices usually do not operate in full density air or other shield-
18 ing gases because the beam scatters and loses energy quickly in the
19 air, and contamination from the workpiece vapors can damage the
20 cathode. A vacuum-air interface, usually a differential pumping
21 apparatus referred to as an aerodynamic window, maintains the high
22 vacuum required in the electron source. However, pulsed electron
23 beams can often be transported in a self-pinched state through
24 dense gases, thus minimizing beam expansion. In addition, since
25 the fraction of time or duty cycle during which the beam is turned
26 on is small ($<10^{-3}$ in most cases), the window can be shuttered

1 between pulses. This should reduce pumping requirements and reduce
2 the flow of workpiece vapors back into the electron source.

3 The electron beam system described above with respect to
4 Figure 2 encompasses a variety of beam source options. The details
5 of the beam source are not important provided that the beam source
6 can produce a current and energy history which matches the thick-
7 ness of the ablator and coating layers.

8 In demonstrating the present invention, the applicants used a
9 single pulse, long pulse modulator and a carbon fiber cathode. In
10 high average power versions, such a device would require switches
11 capable of operating at repetition rates of 10-1000 Hz. Several
12 options exist for switches, including spark gaps, thyratrons, and
13 solid state devices, and there has been considerable recent prog-
14 ress in improving the reliability and life cycles of both thyratron
15 and solid state switches. Carbon fiber cathodes are not essential,
16 but they appear to be particularly well-suited to industrial
17 applications because they can survive for many pulses ($\gg 10^6$), are
18 relatively insensitive to poisoning and vacuum constraints, and can
19 produce longer pulses without collapsing than most other designs.
20 It may also be desirable in some cases to have separate high and
21 low voltage electron beam sources, rather than relying on complex
22 pulse shaping from a single beam source.

23 The ablator layer can in principle be any easily-vaporized
24 material which is thick enough to stop most of the low energy
25 electrons at the tail of the pulse while allowing the high energy
26 electrons to heat the coating. Metals such as tin and zinc as well

1 as certain organics such as polyethylene or phenols appear to be
2 suitable for most applications. Thermal spray coatings encompass
3 a very wide array of materials, including metals, alloys, ceramics,
4 and carbides. The same coatings can be applied to virtually any
5 substrate because the process normally heats the substrate by less
6 than 300°. Electron beam ablative bonding has similar flexibility.

7 Many variations and modifications of the above described
8 embodiments of the present invention will become apparent to those
9 of ordinary skill in the art from a reading of this disclosure. It
10 should be realized that the invention is not limited to the partic-
11 ular apparatus disclosed.

ABSTRACT OF THE DISCLOSURE

A method and apparatus for bonding a layer of coating or cladding material onto a substrate with minimal bulk heating of the substrate. A pulsed electron beam generator is used to produce high energy electrons at the beginning of the pulse and a larger number of lower energy electrons at the end of the pulse. A thin sacrificial or ablative layer of an easily-vaporized material such as tin is placed on top the coating. The high energy electrons penetrate through the ablative and coating layers and heat the coating-substrate interface. The ablative layer is then heated by the low energy electrons to a much higher temperature, causing it to vaporize. The ablation process generates a force on the coating layer which drives it into the substrate.

Fig. 1 Overview of Ablative Bonding Process

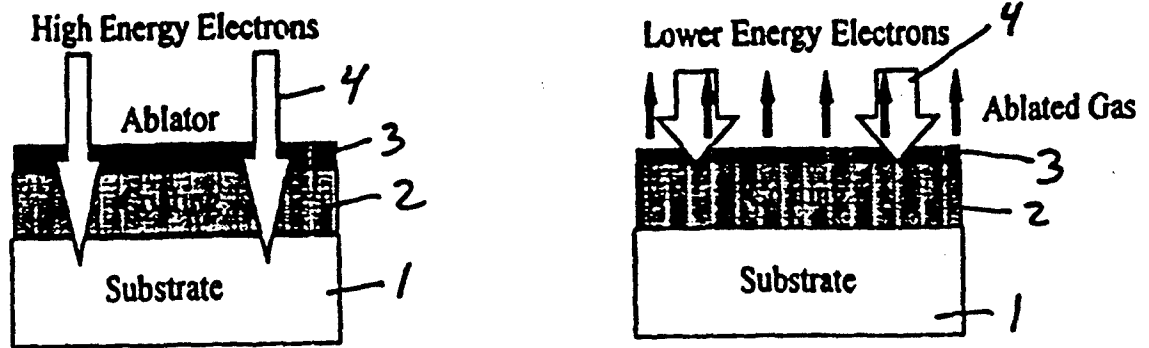


Fig. 2 Generic Components of Ablative Bonding System

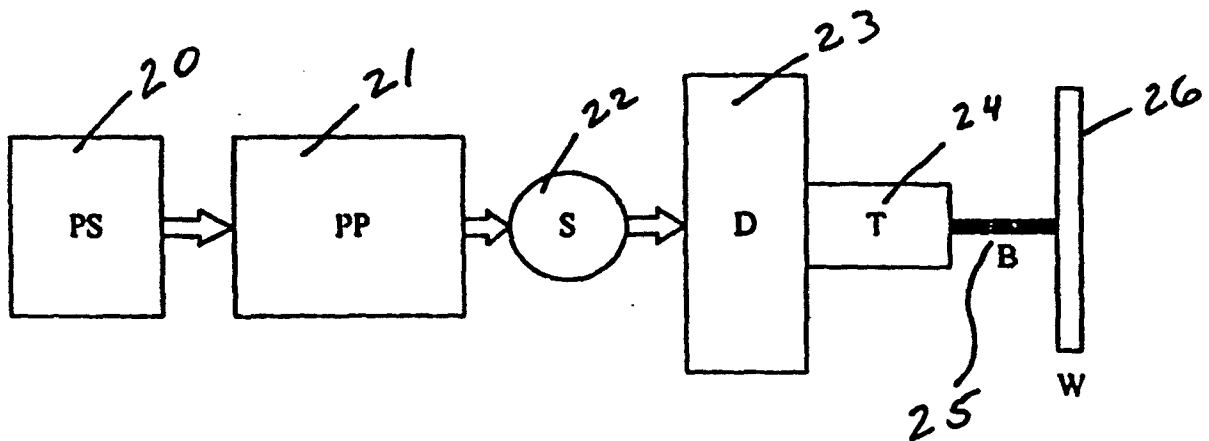


Fig. 3. Electron Range In Various Materials

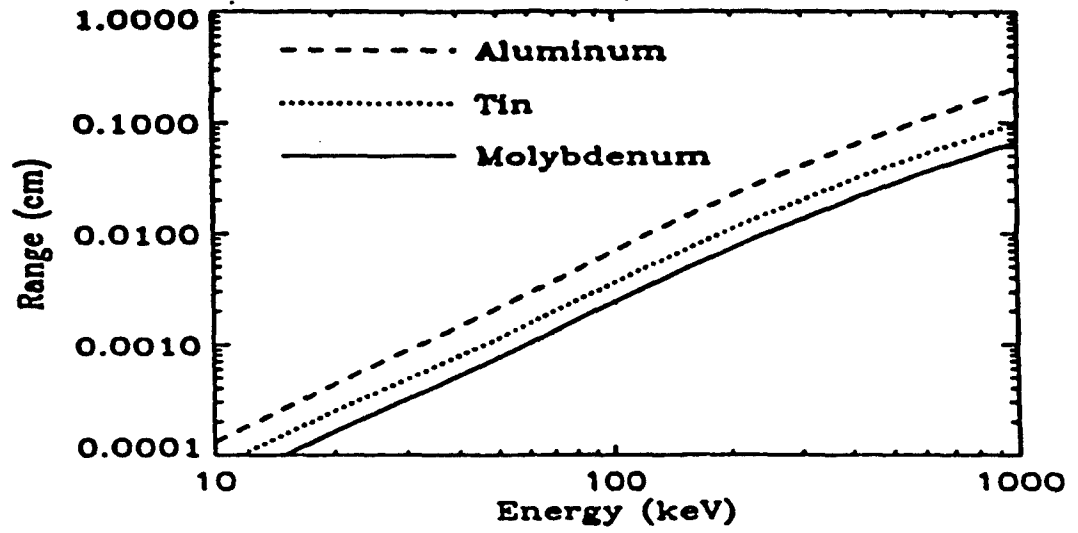


Fig. 4 Ablative Bonding Experimental Configuration.

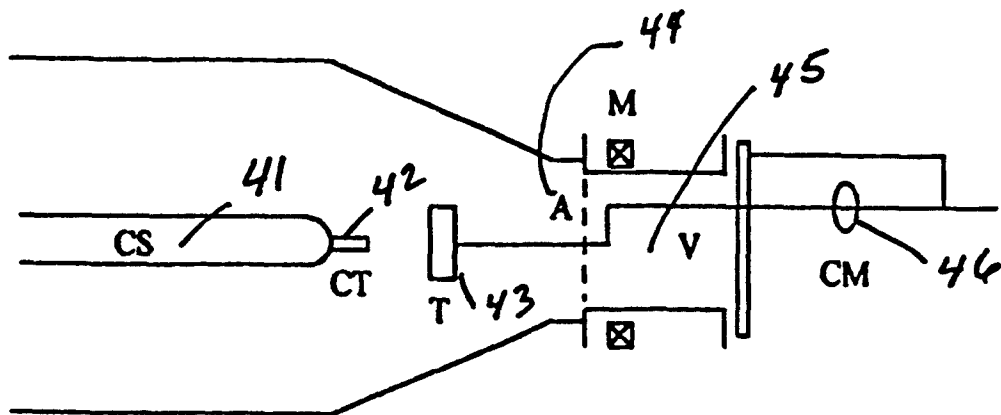


Fig. 5. Voltage and Current vs Time from Ablative Bonding Experiment

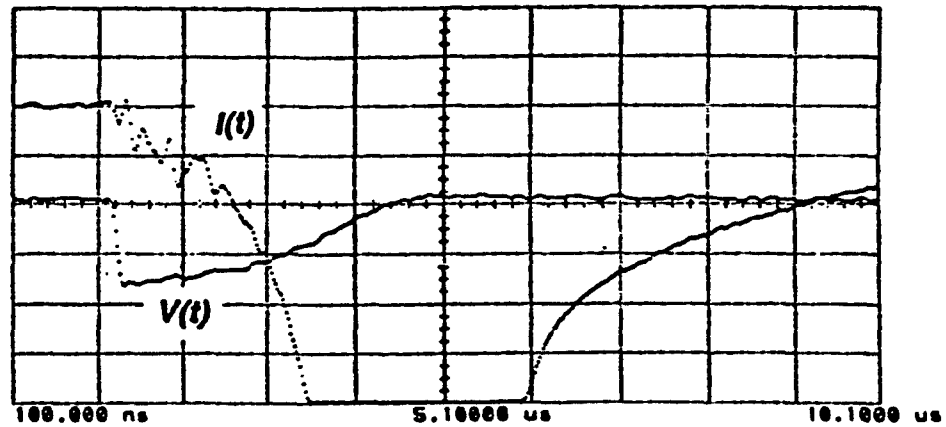


Figure 6

